# DISCRETE SEMICONDUCTORS

# DATA SHEET

# BT151U series C Thyristors

**Product specification** 

August 2018



# **Thyristors**

static switching.

# BT151U series C

# **GENERAL DESCRIPTION**

# Passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and

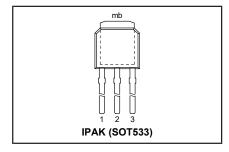
# **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V <sub>DRM</sub> , V <sub>RRM</sub> I <sub>T(AV)</sub> I <sub>T(RMS)</sub> I <sub>TSM</sub>	BT151U- Repetitive peak off-state voltages Average on-state current RMS on-state current Non-repetitive peak on-state current	<b>500C</b> 500 7.5 12 100	650C 650 7.5 12 100	800C 800 7.5 12 100	V A A A

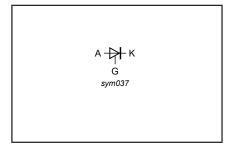
# **PINNING - SOT533, (I-PAK)**

PIN NUMBER	DESCRIPTION
1	cathode
2	anode
3	gate
tab	anode

# **PIN CONFIGURATION**



# **SYMBOL**



# **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V <sub>DRM</sub> , V <sub>RRM</sub>	Repetitive peak off-state voltages		-	<b>-500C</b> 500 <sup>1</sup>	<b>-650C</b> 650 <sup>1</sup>	<b>-800C</b> 800	V
$\begin{matrix} I_{T(AV)} \\ I_{T(RMS)} \\ I_{TSM} \end{matrix}$	Average on-state current RMS on-state current Non-repetitive peak on-state current	half sine wave; $T_{mb} \le 104 ^{\circ}\text{C}$ all conduction angles half sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge	- -		7.5 12		A A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t = 10 ms t = 8.3 ms t = 10 ms	- - -		100 110 50		A A A <sup>2</sup> s
dl <sub>⊤</sub> /dt	Repetitive rate of rise of on-state current after triggering	$I_{TM} = 20 \text{ A}; I_{G} = 50 \text{ mA}; dI_{G}/dt = 50 \text{ mA/}\mu\text{s}$	-		50		A/μs
$egin{array}{c} I_{GM} \ V_{RGM} \ P_{GM} \end{array}$	Peak gate current Peak reverse gate voltage Peak gate power		- - -		2 5 5		A V W
P <sub>G(AV)</sub> T <sub>stg</sub> T <sub>j</sub>	Average gate power Storage temperature Junction temperature	over any 20 ms period	-40 -		0.5 150 125		ů Č M

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

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# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	Thermal resistance junction to mounting base Thermal resistance	in free air	-	- 70	1.3	K/W K/W K/W
ιτη-α	junction to ambient					

# STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$	-	2	15	mA
l I <sub>L</sub>	Latching current	$V_D^{\rm p} = 12 \text{ V}; I_{\rm GT}^{\rm r} = 0.1 \text{ A}$	-	10	40	mA
l i <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	7	20	mA
ĺΫ́	On-state voltage	$I_{T} = 23 \text{ A}$	-	1.44	1.75	V
V <sub>GT</sub>	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.6	1.5	V
		$V_D = V_{DRM(max)}$ ; $I_T = 0.1 \text{ A}$ ; $T_j = 125 ^{\circ}\text{C}$	0.25	0.4	-	V
I <sub>D</sub> , I <sub>R</sub>	Off-state leakage current	$V_D = V_{DRM(max)}^{Station (max)}; V_R = V_{RRM(max)}; T_j = 125 °C$	-	0.1	0.5	mA

# **DYNAMIC CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% \ V_{DRM(max)}; \ T_j = 125 \ ^{\circ}C;$ exponential waveform Gate open circuit $R_{GK} = 100 \ \Omega$	50 200	130 1000	- -	V/μs V/μs
t <sub>gt</sub> t <sub>q</sub>	Gate controlled turn-on time Circuit commutated turn-off time	$\begin{array}{l} I_{TM} = 40 \text{ A; } V_D = V_{DRM(max)}; \ I_G = 0.1 \text{ A; } \\ dI_G/dt = 5 \text{ A/}\mu s \\ V_D = 67\% \ V_{DRM(max)}; \ T_j = 125 \ ^{\circ}\text{C; } \\ I_{TM} = 20 \text{ A; } V_R = 25 \text{ V; } dI_{TM}/dt = 30 \text{ A/}\mu s; \\ dV_D/dt = 50 \text{ V/}\mu s; \ R_{GK} = 100 \ \Omega \end{array}$	-	2 70	-	μs μs

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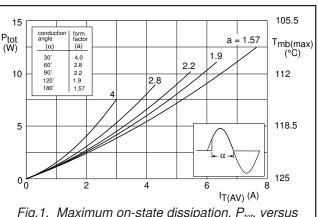


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus average on-state current,  $I_{T(AV)}$ , where  $a = form \ factor = I_{T(RMS)} / I_{T(AV)}$ .

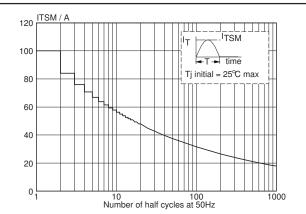


Fig.4. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

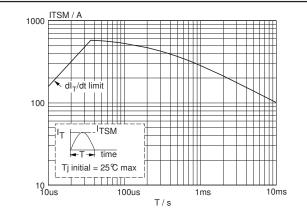


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 10$ ms.

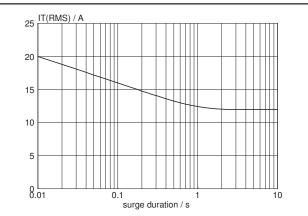


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 100$  °C.

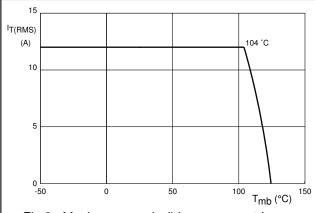
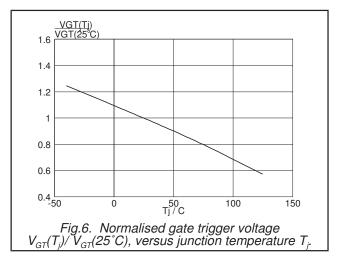
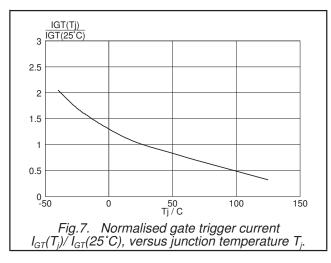
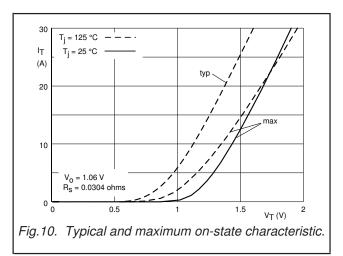


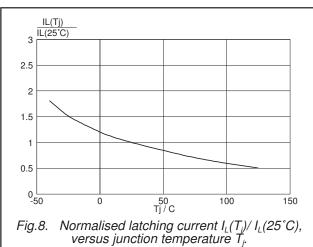
Fig.3. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

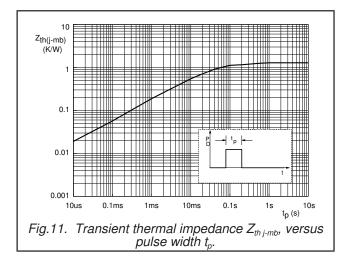


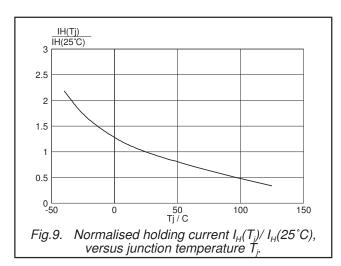
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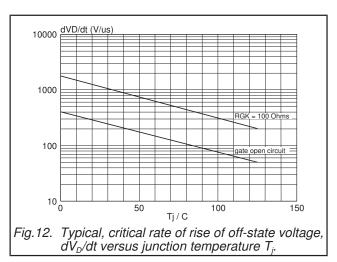












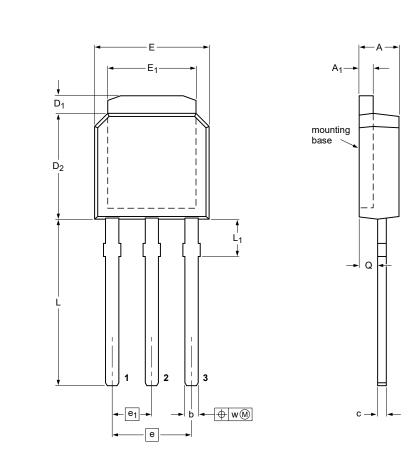
**Thyristors** 

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# **MECHANICAL DATA**



SOT533



# **DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	C	D <sub>1</sub>	D <sub>2</sub>	E	E <sub>1</sub>	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(2)</sup> max	ď	w
mm										2.285 BSC <sup>(1)</sup>		2.7	1.1 1.0	0.3

#### Notes

- 1. Basic spacing between centers.
- 2. Terminal dimensions are uncontrolled within zone L<sub>1</sub>.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT533		TO-251				<del>-05-02-11</del> 06-02-14

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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